# Onsemi

## **IGBT** Die

## NGTD21T65F2

Trench Field Stop II IGBT Die for motor drive and inverter applications.

#### Features

- Extremely Efficient Trench with Field Stop Technology
- Low V<sub>CE(sat)</sub> Loss Reduces System Power Dissipation

#### **Typical Applications**

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

#### **MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^{\circ}C$	V <sub>CE</sub>	650	V
DC Collector Current, limited by $T_{J(\text{max})}$	Ι <sub>C</sub>	(Note 1)	A
Pulsed Collector Current (Note 2)	I <sub>C, pulse</sub>	200	А
Gate-Emitter Voltage	$V_{GE}$	±20	V
Maximum Junction Temperature	TJ	–55 to +175	°C
Short Circuit Withstand Time, $V_{GE}$ = 15 V, $V_{CE}$ = 500V, $T_J$ $\leq$ 150°C	T <sub>SC</sub>	5.0	μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Depending on thermal properties of assembly.

- 2.  $T_{pulse}$  limited by  $T_{jmax}$ , 10 µs pulse,  $V_{GE}$  = 15 V.

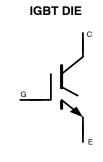
#### **MECHANICAL DATA**

Parameter	Value	Unit	
Die Size	4451 x 4451	μm <sup>2</sup>	
Emitter Pad Size	See die layout	μm <sup>2</sup>	
Gate Pad Size	410 x 570	μm <sup>2</sup>	
Die Thickness	3	mils	
Wafer Size	150	mm	
Top Metal	4 μm AISI		
Back Metal	2 μm TiNiAg		
Max Possible Chips per Wafer	630		
Passivation Frontside	Oxide-Nitride		
Reject Ink Dot Size	25 mils		
Recommended Storage Environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Die on tape in ring-pack Storage time: < 3 months		

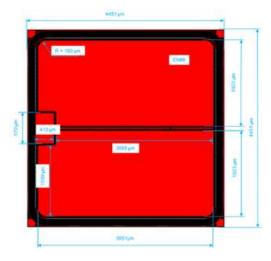
#### **ORDERING INFORMATION**

Device	Inking?	Shipping
NGTD21T65F2WP	Yes	Bare Wafer on Tape
NGTD21T65F2SWK	Yes	Sawn Wafer on Tape

V<sub>RCE</sub> = 650 V  $I_{C}$  = Limited by  $T_{J(max)}$ 







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### NGTD21T65F2

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ , unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units	
STATIC CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	$V_{GE}$ = 0 V, I <sub>C</sub> = 500 $\mu$ A	V <sub>(BR)CES</sub>	650			V	
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 45 A	V <sub>CE(sat)</sub>		1.7	1.9	V	
Gate-Emitter Threshold Voltage	$V_{GE}$ = $V_{CE}$ , $I_C$ = 350 $\mu$ A	V <sub>GE(TH)</sub>	4.5	5.5	6.5	V	
Collector-Emitter Cutoff Current	$V_{GE}$ = 0 V, $V_{CE}$ = 650 V	I <sub>CES</sub>			0.5	mA	
Gate Leakage Current	$V_{GE}$ = 20 V, $V_{CE}$ = 0 V	I <sub>GES</sub>			200	nA	
DYNAMIC CHARACTERISTICS							
Input Capacitance	$V_{CE} = 20 \text{ V}, \text{ V}_{GE} = 0 \text{ V},$	C <sub>ies</sub>		5328		pF	
Output Capacitance	— f = 1 MHz	C <sub>oes</sub>		252		pF	

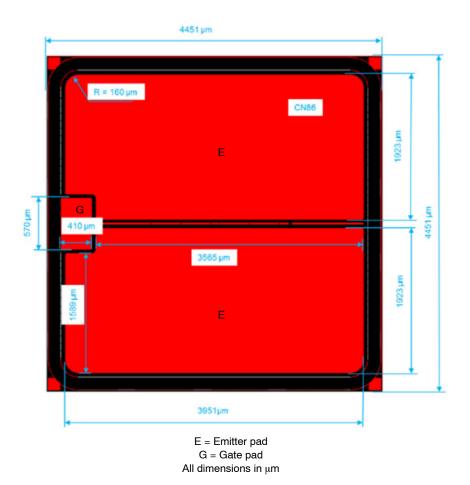
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

C<sub>res</sub>

pF

148

#### DIE LAYOUT



#### Further Electrical Characteristic

Reverse Transfer Capacitance

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

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